



N-Channel Depletion-Mode MOSFET



SOT-23



Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(\Omega)(max)$	I _D (A)
600	700 @ V _{GS} = 0V	0.03

Features

- Depletion Mode
- Low Gate Charge

Application

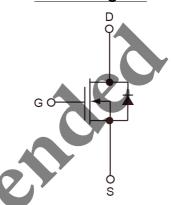
- Converters
- Telecom

Ordering Information

Part No.	Package	Packing
TSM126CX RFG	SOT-23	3kpcs / 7" Reel

Note: "G" denotes Halogen Free Product.

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current Tc=25℃		0.030	Α
Continuous Drain Current Tc=70℃	I _D	0.024	Α
Pulsed Drain Current ^a	I _{DM}	0.120	Α
Maximum Power Dissipation	P _D	0.5	W
Soldering Temperature b	T_L	300	°C
Operating Junction Temperature	T _J	+150	°C
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction to Ambient	$R\Theta_{JA}$	250	°C/W

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Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Distance of 1.6mm from case for 10 seconds.

Version: A14



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Electrical Specifications (Tj = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static ^a				I.		
Drain-Source Breakdown Voltage	$V_{GS} = -5V, I_D = 250\mu A$	BV _{DSS}	600			V
Gate Threshold Voltage	$V_{DS} = 3V, I_{D} = 8\mu A$	$V_{GS(TH)}$	-2.7	-1.8	-1.0	V
Drain-Source cutoff current	$V_{DS} = 600V, V_{GS} = -5V,$ $Ta = 25^{\circ}C$				0.1	μA
Drain-Source cutoff current	V_{DS} = 480V, V_{GS} = -5V, Ta = 125°C	I _{DS(OFF)}		7	10	μA
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}	^		±10	μA
On-state Drain Current	$V_{DS} = 25V, V_{GS} = 0V$	I _{DSS}	12	K		mA
	$V_{GS} = 0V$, $I_D = 3mA$		(350	700	Ω
Drain-Source On-State Resistance	V _{GS} = 10V, I _D = 16mA	$R_{DS(ON)}$		400	800	Ω
Forward Transconductance	$ V_{DS} > 2 I_{D} R_{DS(ON)max},$ $I_{D} = 0.01A$	g _{fs}	0.008	0.017		S
Dynamic	<u> </u>			I.		
Input Capacitance		C _{iss}		51.42		
Output Capacitance	$V_{DS} = 25V, V_{GS} = -5V,$	C _{oss}		4.48		pF
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}		1.12]
Total Gate Charge	V = 400V I = 20VA	Q_g		1.18		
Gate-Source Charge	$V_{DS} = 400V, I_D = 0.01A,$ $V_{GS} = -5V \text{ to } 5V$	Q_gs		0.49		nC
Gate-Drain Charge	V _{GS} = -5V to 5V	Q_gd		0.365		
Switching						
Turn-On Delay Time	V 2000V I 0044	t _{d(on)}		10.01	-	
Turn-On Rise Time	$V_{DD} = 300V, I_D = 0.01A,$	t _r		55.7		
Turn-Off Delay Time	$V_{GS} = -5V$ to $7V$,	$t_{d(off)}$		57.2		ns
Turn-Off Fall Time	$R_G = 6\Omega$	t _f 135.	135.5			
Source-Drain Diode	•					
Diode forward Current	Continuous	Is			0.025	Α
Diode Pulse Current		I _{SM}			0.100	Α
Diode Forward Voltage	I _{SD} = 16mA, V _{GS} = -5V	V_{SD}			1.2	V
Reverse Recovery Time	I _F =0.01A, V _{GS} =-10V	trr		243.1		ns
Reverse Recovery Charge	dI _F /dt=100A/μs, V _R =30V	Qrr		639		nC

Notes:

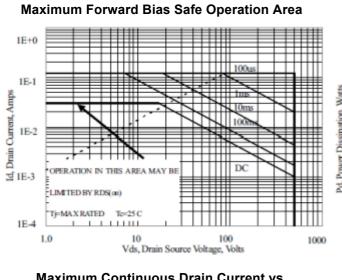
a. pulse test: PW $\leqslant\!380\mu s,$ duty cycle $\leqslant\!2\%$



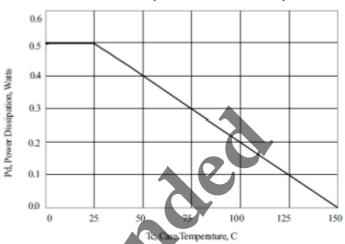
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Electrical Characteristics Curves (Ta = 25°C, unless otherwise noted)

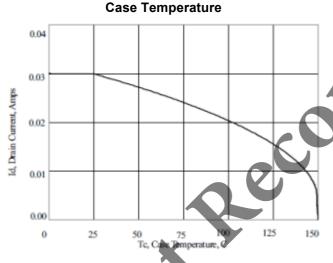


Maximum Power Dissipation vs. Case Temperature

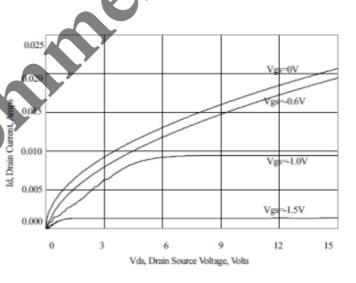


Maximum Continuous Drain Current vs.

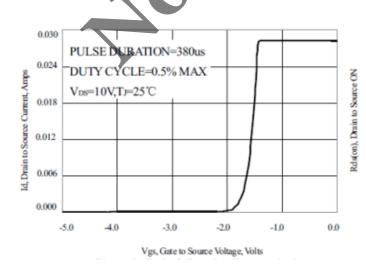




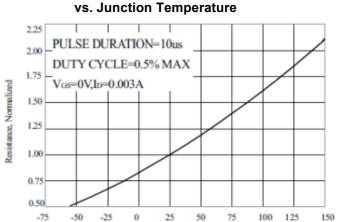
Typical Output Characteristics



Typical Transfer Characteristics



Drain to Source ON Resistance



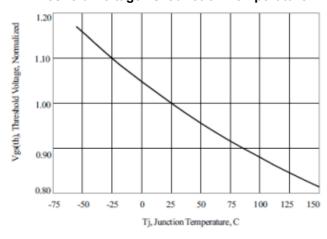
Tj, Junction Temperature, C

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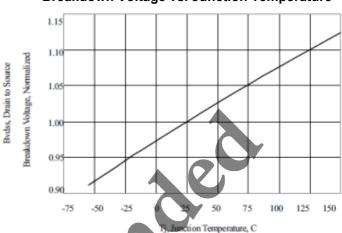


Electrical Characteristics Curves (Ta = 25°C, unless otherwise noted)

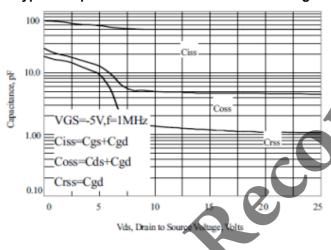
Threshold Voltage vs. Junction Temperature



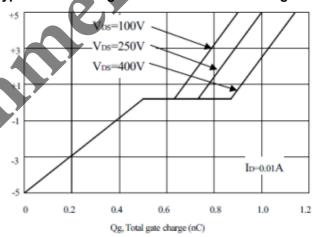
Breakdown Voltage vs. Junction Temperature



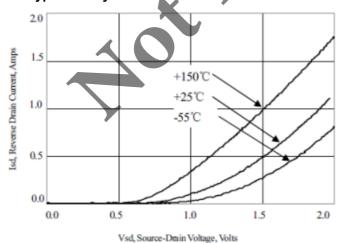
Typical Capacitance vs. Drain to source Voltage



Typical Gate Charge vs. Gate to Source Voltage



Typical Body Diode Transfer Characteristics



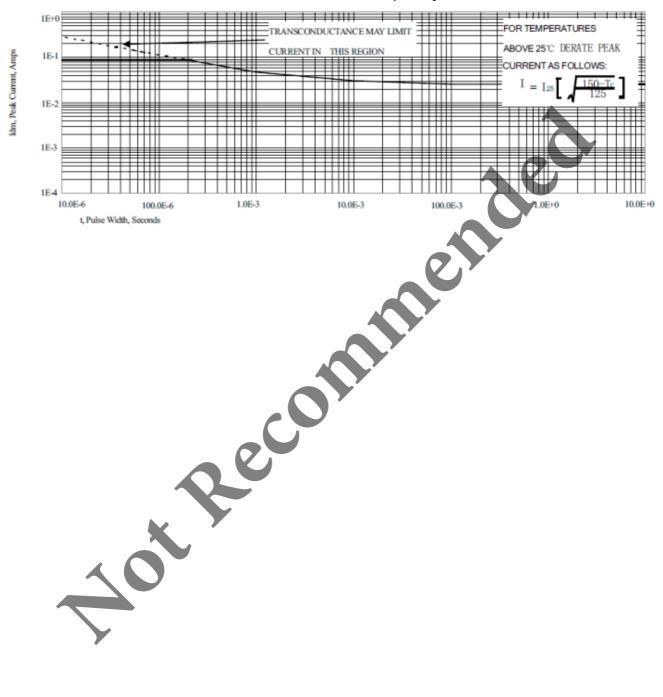




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Electrical Characteristics Curves (Ta = 25°C, unless otherwise noted)

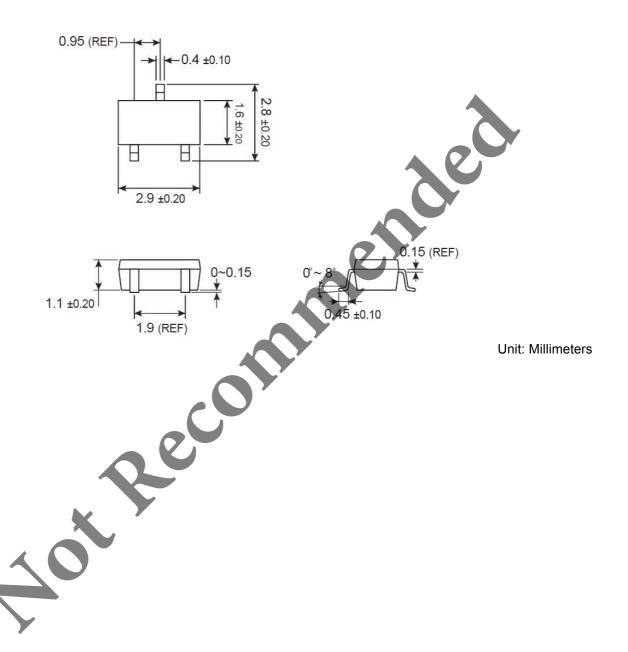
Maximum Peak Current Capability







SOT-23 Mechanical Drawing



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